

EAST - [10.658442.wsp:1]

FileViewEditToolsWindowHelp

Drafts

Pending

Active

L1: (8) "6806262"

L2: (168) (PERNER near2 FREDERICK).in.

L3: (1136) 365/158

L4: (1251) 365/171

L5: (878) 365/173

L6: (215692) 365/

L8: (43066) MRAM or ((magnetoresistive or (magneto-resistive) or magnetic) near3 memory)

L9: (11732) (writ\$4 or program\$4) with current with generat\$4

L10: (129) test\$4 near5 (magnetic or magnetoresistive or magneto-resistive) near5 cell

L11: (10) 9 and 10

L12: (22) 8 and 10

L14: (42) dummy near5 (magnetic or magnetoresistive or magneto-resistive) near5 cell

L15: (24) 9 and 14

L16: (20) 15 not (12 or 11)

L17: (106) 10 not (11 or 12 or 14)

L18: (316) 3 and 9

L19: (1129) 8 and 9

L20: (305) 3 and 19

L21: (128) easy with axis with writ\$4 with current

L22: (101) hard with axis with writ\$4 with current

L23: (31) 20 and 21

L25: (29) 20 and 22

L26: (12) 25 not 23

L29: (275) 4 and 19

L30: (75) 29 not 20

L33: (236) 5 and 19

L34: (47) 33 not 29

L35: (615) 6 and 19

L36: (216) 35 not (20 or 29 or 33)

L39: (10) (OKANO near2 KAZUHISA).in.

ResearchWitBrowseQueueClear

DBsUSPAT: US-PGPUB, EPO, JPO, DERWENT: IBM_TDB

Default operator: OR

Highlight all hit terms initially

	U	1	2	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 2003115577 A	20030418	7	NONVOLATILE MAGNETIC THIN FLM MEMORY				OKANO, KAZUHISA	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6594191 B2	20030715	13	Segmented write line architecture	365/225.5	365/158; 365/230.06		Lammers, Stefan et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

NUM

11:42 AM